

PROCESS FOR PRODUCING OXIDE FILMS

Abstract of the Disclosure

A process for producing bismuth-containing oxide thin films by Atomic Layer Deposition, including using an organic bismuth compound having at least one silylamido ligand as a source material for the bismuth oxide. Bismuth-containing oxide thin films produced by the preferred embodiments can be used, for example, as ferroelectric or dielectric material in integrated circuits and/or as superconductor materials.

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